

MANUFACTURING METHOD FOR SEMICONDUCTOR DEVICE, AND SEMICONDUCTOR DEVICE

ABSTRACT

Provided are a manufacturing method for a semiconductor device, and a semiconductor device. The manufacturing method comprises: providing a substrate; forming on the substrate multiple first structures extending in a first direction; forming a sacrificial layer on a side surface of each first structure; forming an outer spacing layer on a side surface of each sacrificial layer; removing a part of each outer spacing layer to obtain patterned outer spacing layers, so as to expose a part of each sacrificial layer; and removing the sacrificial layers to form air gaps between the patterned outer spacing layers and the first structures.

[Fig. 1]